

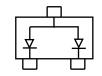
# **SWITCHING DIODE**

### **PRODUCT SUMMARY**

SOD-23 Plastic-Encapsulate Diodes

#### **FEATURES**

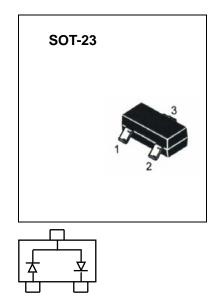
Fast Switching Speed For General Purpose Switching Applications High Conductance







BAV70 Marking: A4



BAV99 Marking: A7



Pb-free; RoHS-compliant

## **MAXIMUM RATINGS** @T<sub>A</sub>=25°C

Parameter	Symbol	Limits	Unit
Reverse voltage	$V_R$	70	V
Forward Current	I <sub>F</sub>	200	mA
Peak Forward Surge Current	I <sub>FM(surge)</sub>	500	mA
Power Dissipation	P <sub>D</sub>	225	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	556	°C/W
Junction temperature	TJ	150	°C
Storage temperature range	T <sub>STG</sub>	-55-150	°C

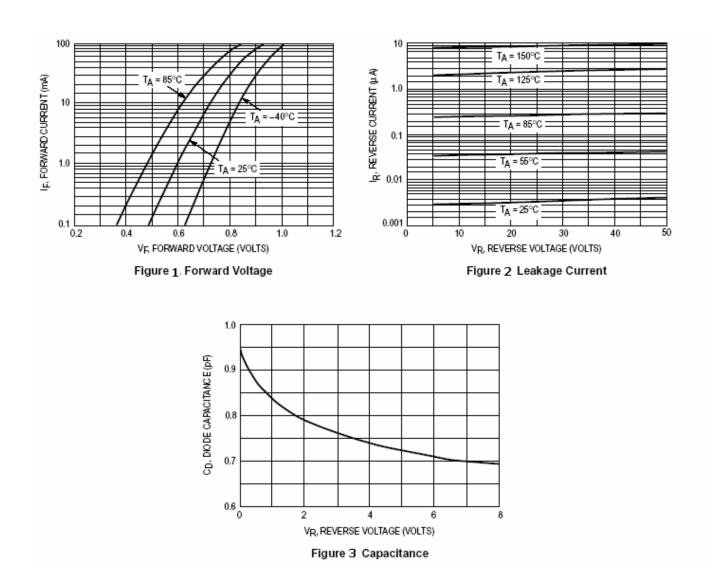


# **ELECTRICAL CHARACTERISTICS** @T<sub>A</sub>=25°C

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V <sub>R</sub>	70			V	I <sub>R</sub> =100μA
Forward voltage	V <sub>F1</sub>			0.715	V	I <sub>F</sub> =1mA
	V <sub>F2</sub>			0.855	V	I <sub>F</sub> =10mA
	V <sub>F3</sub>			1	V	I <sub>F</sub> =50mA
	$V_{F4}$			1.25	٧	I <sub>F</sub> =150mA
Reverse current	I <sub>R</sub>			2.5	μΑ	V <sub>R</sub> =70V
Capacitance between terminals	C <sub>T</sub>			1.5	pF	V <sub>R</sub> =0,f=1MHz
Reverse recovery time	trr			6	ns	$I_F = I_R = 10 \text{mA},$
						Irr= $0.1 \times I_R$ , $R_L = 100\Omega$



#### TYPICAL CHARACTERISTICS



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